## NSN 5962-01-335-9754

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View Online at https://aerobasegroup.com/nsn/5962-01-335-9754

view Offilitie at https://derobasegroup.com/hsh/osoz-o1-oso-s7-o4
Body Length:
Between 0.342 inches and 0.358 inches
Body Width:
Between 0.342 inches and 0.358 inches
Body Height:
Between 0.060 inches and 0.100 inches
Maximum Power Dissipation Rating:
303.0 milliwatts
Operating Tempurature Range:
-55.0/+125.0 degrees celsius
Storage Tempurature Range:
-65.0/+150.0 degrees celsius
Features Provided:
Burn in and bipolar and electrostatic sensitive and monolithic and programmed
Inclosure Material:
Ceramic
Inclosure Configuration:
Leadless flat pack
Output Logic Form:
Transistor-transistor logic
Input Circuit Pattern:
12 input
Case Outline Source And Designator:
C-2 mil-m-38510
Terminal Surface Treatment:
Solder
Voltage Rating And Type Per Characteristic:
-0.5 volts power source and 7.0 volts power source
Time Rating Per Chacteristic:
50.00 nanoseconds propagation delay time, low to high level output and 50.00 nanoseconds propagation delay time, high to low lev
output
Memory Device Type:
Pal
Test Data Document:
96906-mil-std-883 standard (includes industry or association standards, individual manufactureer standards, etc.).
Terminal Type And Quantity:
20 leadless
Shelf Life:
N/a
Unit Of Measure:

Yes - demil/mli

Demilitarization:

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